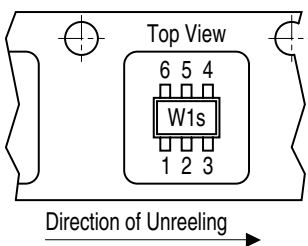
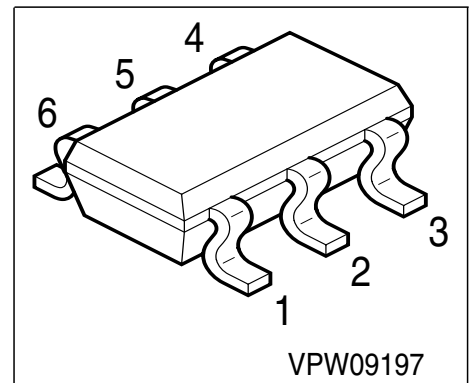


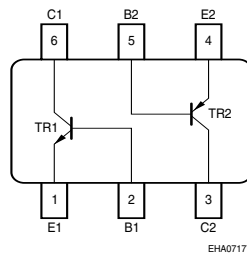
**NPN/PNP Silicon Transistor Array**

- For AF input stages and driver applications
- High current gain
- Low collector-emitter saturation voltage
- Two (galvanic) internal isolated NPN/PNP Transistors in one package

**Tape loading orientation**


Marking on SC74 package (for example W1s) corresponds to pin 1 of device

Position in tape: pin 1 opposite of feed hole side



SC74\_Tape

EH407177

Type	Marking	Pin Configuration					Package	
BC817UPN	1Bs	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SC74

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CEO}$	45	V
Collector-base voltage	$V_{CBO}$	50	
Emitter-base voltage	$V_{EBO}$	5	
DC collector current	$I_C$	500	mA
Peak collector current	$I_{CM}$	1	A
Base current	$I_B$	100	mA
Peak base current	$I_{BM}$	200	
Total power dissipation, $T_S = 115\text{ °C}$	$P_{tot}$	330	mW
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-65 ... 150	

**Thermal Resistance**

Junction - soldering point <sup>1)</sup>	$R_{thJS}$	≤105	K/W
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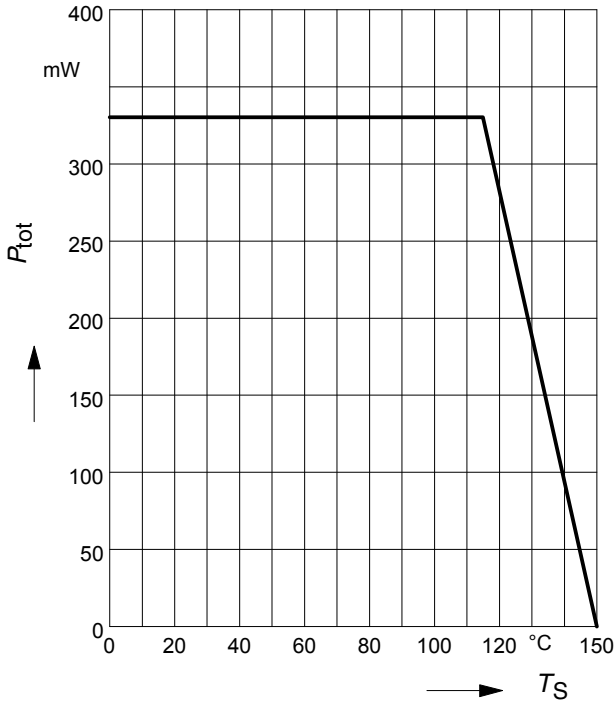
<sup>1)</sup>For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance

**Electrical Characteristics at  $T_A=25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC Characteristics</b>					
Collector-emitter breakdown voltage $I_C = 10\text{ mA}, I_B = 0$	$V_{(BR)CEO}$	45	-	-	V
Collector-base breakdown voltage $I_C = 10\text{ }\mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	50	-	-	
Emitter-base breakdown voltage $I_E = 10\text{ }\mu\text{A}, I_C = 0$	$V_{(BR)EBO}$	5	-	-	
Collector cutoff current $V_{CB} = 25\text{ V}, I_E = 0$	$I_{CBO}$	-	-	100	nA
Collector cutoff current $V_{CB} = 25\text{ V}, I_E = 0, T_A = 150\text{ }^\circ\text{C}$	$I_{CBO}$	-	-	50	$\mu\text{A}$
Emitter cutoff current $V_{EB} = 4\text{ V}, I_C = 0$	$I_{EBO}$	-	-	100	nA
DC current gain 1) $I_C = 100\text{ mA}, V_{CE} = 1\text{ V}$ $I_C = 300\text{ mA}, V_{CE} = 1\text{ V}$	$h_{FE}$	160 100	250 -	400 -	-
Collector-emitter saturation voltage1) $I_C = 500\text{ mA}, I_B = 50\text{ mA}$	$V_{CEsat}$	-	-	0.7	V
Base-emitter saturation voltage 1) $I_C = 500\text{ mA}, I_B = 50\text{ mA}$	$V_{BEsat}$	-	-	1.2	
<b>AC Characteristics</b>					
Transition frequency $I_C = 50\text{ mA}, V_{CE} = 5\text{ V}, f = 100\text{ MHz}$	$f_T$	-	170	-	MHz
Collector-base capacitance $V_{CB} = 10\text{ V}, f = 1\text{ MHz}$	$C_{cb}$	-	6	-	pF
Emitter-base capacitance $V_{EB} = 0.5\text{ V}, f = 1\text{ MHz}$	$C_{eb}$	-	60	-	

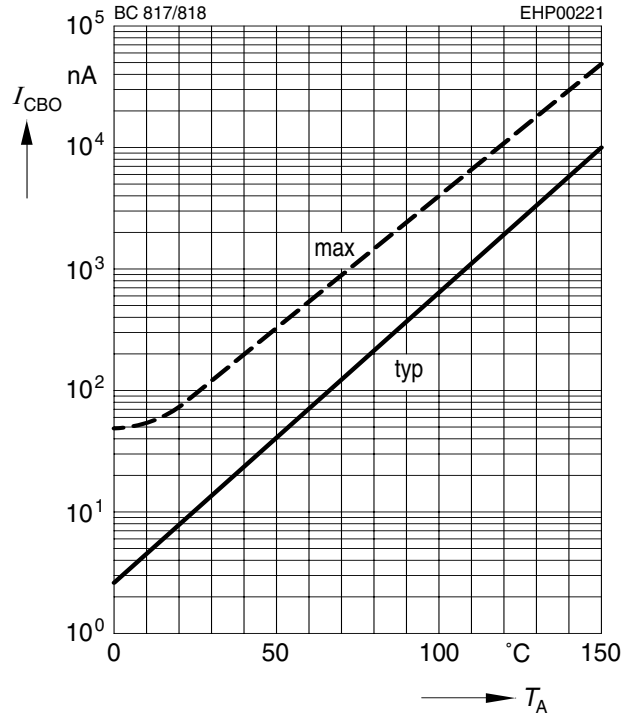
 1) Pulse test:  $t < 300\mu\text{s}$ ;  $D < 2\%$

**Total power dissipation  $P_{tot} = f(T_S)$**

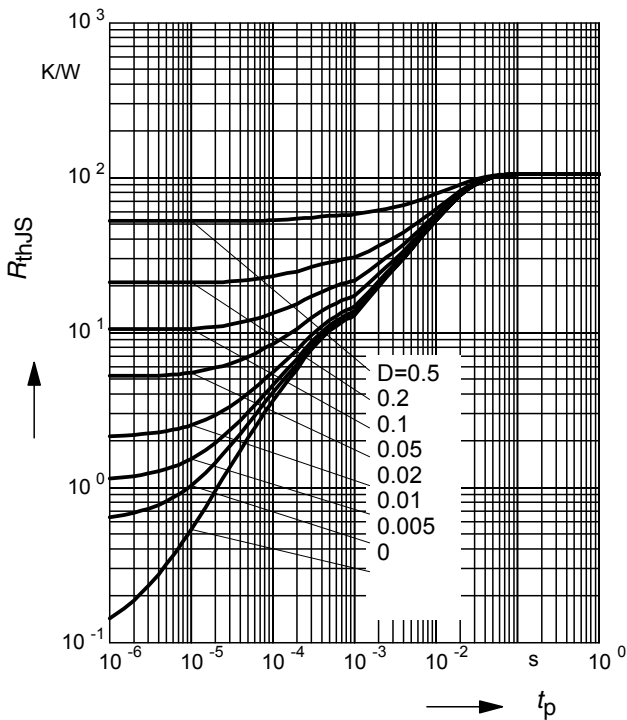


**Collector cutoff current  $I_{CBO} = f(T_A)$**

$V_{CB} = 25V$

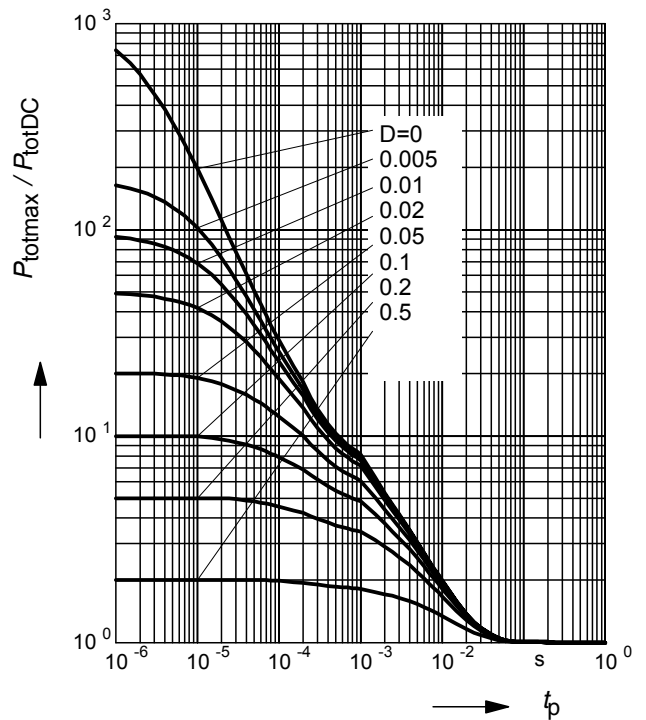


**Permissible Pulse Load  $R_{thJS} = f(t_p)$**



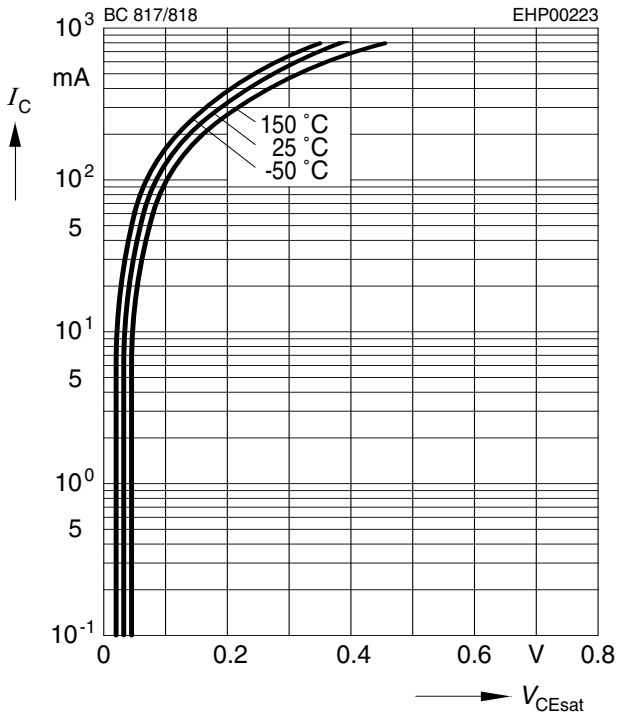
**Permissible Pulse Load**

$P_{totmax} / P_{totDC} = f(t_p)$



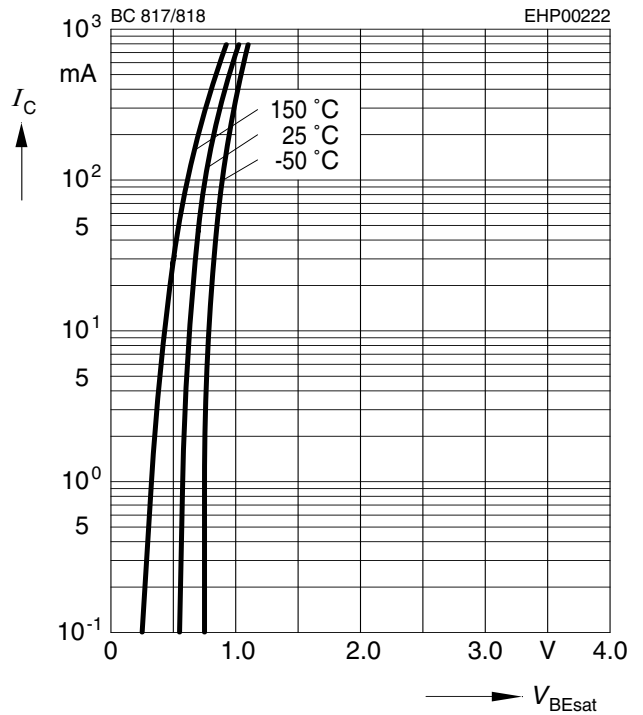
**Collector-emitter saturation voltage**

$I_C = f(V_{CEsat}), h_{FE} = 10$



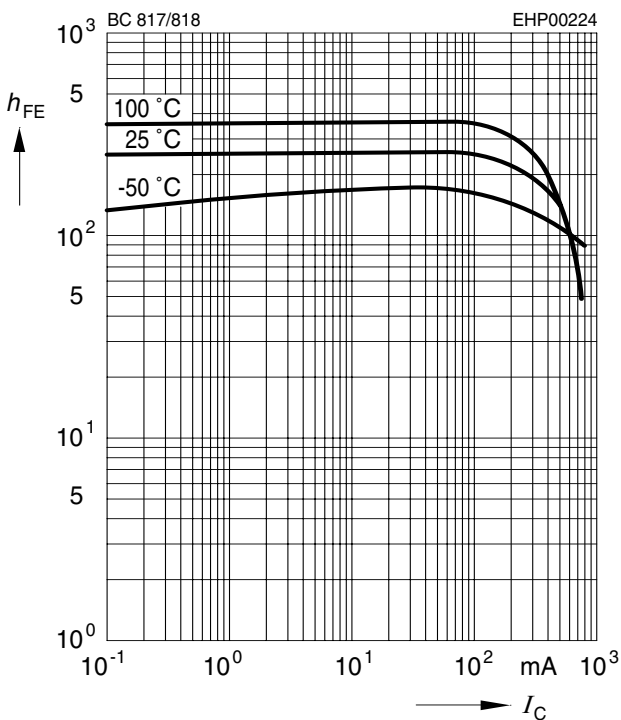
**Base-emitter saturation voltage**

$I_C = f(V_{BEsat}), h_{FE} = 10$



**DC current gain  $h_{FE} = f(I_C)$**

$V_{CE} = 5V$



**Transition frequency  $f_T = f(I_C)$**

$V_{CE} = 5V$

